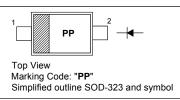
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

For super-high speed switching and wave detection circuit applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM} 30		V
Reverse Voltage	V_R	30	V
Forward Current	I _F	30	mA
Peak Forward Current	I _{FM}	I _{FM} 150	
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

Characteristics at $T_a = 25$ °C

Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 30 \text{ mA}$	V _F	- -	0.4 1	٧
Reverse Current at V _R = 30 V	I _R	-	0.3	μΑ
Terminal Capacitance at V _R = 1 V, f = 1 MHz	Ст	1.5	-	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{rr} = 1$ mA, $R_L = 100$ Ω	t _{rr}	1	-	ns
Detection Efficiency at V_{in} = 3 $V_{(peak)}$, f = 30 MHz, R_L = 3.9 K Ω , C_L = 10 pF	η	65	-	%



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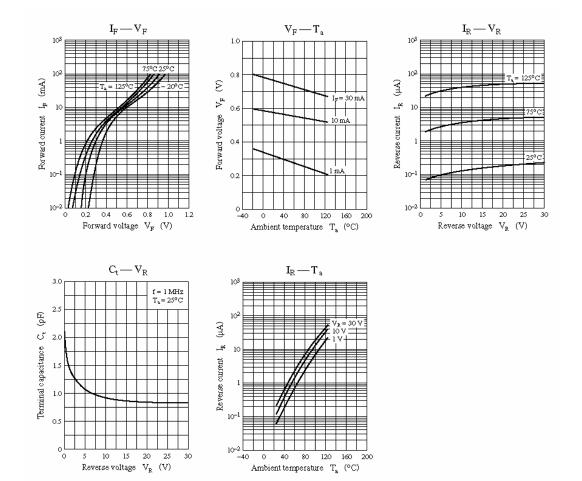
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Dated: 01/09/2006





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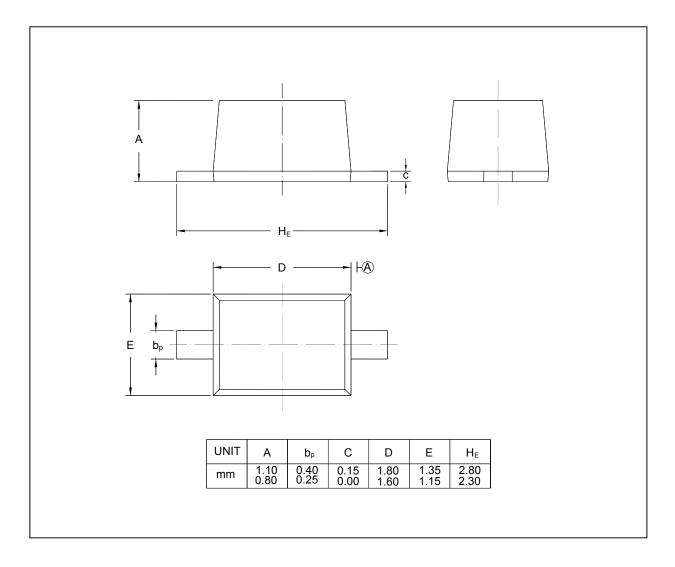


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323





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